

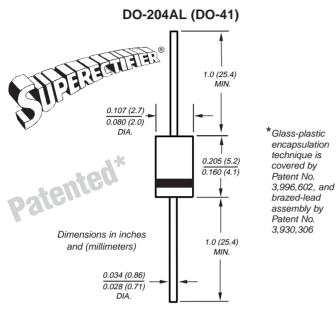
New Product

Vishay Semiconductors formerly General Semiconductor

Glass Passivated Ultrafast Rectifier



SBYV26C



Features

- High temperature metallurgically bonded construction
- Cavity-free glass passivated junction
- Ultrafast recovery time for high efficiency
- Low forward voltage, high current capability
- Capable of meeting environmental standards of MIL-S-19500
- Hermetically sealed package
- Low leakage current High surge current capability
- Specified reverse surge capability
- High temperature soldering guaranteed: 350°C/10 seconds, 0.375" (9.5mm) lead length,5 lbs. (2.3kg) tension

Mechanical Data

Case: JEDEC DO-204AL, molded plastic over glass body Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026 Polarity: Color band denotes cathode end Mounting Position: Any Weight: 0.012 oz., 0.3 g

Maximum Ratings and Thermal Characteristics (TA = 25°C unless otherwise noted)

| 3 | | | |
|---|--------------|-------------|------|
| Parameter | Symbol | Value | Unit |
| Maximum repetitive peak reverse voltage | Vrrm | 600 | V |
| Maximum RMS voltage | Vrms | 420 | V |
| Maximum DC blocking voltage | VDC | 600 | V |
| Maximum average forward rectified current 0.375" (9.5mm) lead length at $T_L = 85^{\circ}C$ (See Fig. 1) | IF(AV) | 1.0 | A |
| Peak forward surge current 10ms single half sine-wave superimposed on rated load | IFSM | 30 | А |
| Non repetitive peak reverse energy (Note 1) | Ersm | 5 | mJ |
| Typical thermal resistance (Note 2,3) | Roja Rojl | 70 16 | °C/W |
| Operating junction and storage temperature range | TJ, TSTG | -65 to +175 | °C |

Electrical Characteristics (TA = 25°C unless otherwise noted)

| Minimum avalanche breakdown | voltage at 100µA | Vbr | 600 | V |
|---|---|---------------------|------------|------|
| Maximum instantaneous forward voltage at 1.0A | TJ = 25°C TJ = 175°C | VF | 2.5 1.3 | V |
| Maximum DC reverse current at rated DC blocking voltage | T _A = 25°C T _A = 165°C | I _R | 5.0 150 | μΑ |
| Max. reverse recovery time at IF = 0.5A, IR = 1.0A, Irr = 0.25A | | trr | 30 | ns |
| Maximum junction capacitance at 4.0V, 1MHz | | CJ | 45 | pF |
| Maximum reverse recovery current slope at $I_F = 1A$, $V_R = 30V$, $di_f/dt = -1A/\mu s$ | | di _r /dt | 7 | A/µs |

Notes: (1) Peak reverse energy measured with $8/20\mu s$ surge

(2) Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, mounted on P.C.B. with 0.5 x 0.5" (12 x 12mm) copper pads
(3) Thermal resistance from junction to lead at 0.375" (9.5mm) lead length with both leads attached to heatsink

SBYV26C

Vishay Semiconductors formerly General Semiconductor

Ratings and

Characteristic Curves (TA = 25°C unless otherwise noted)

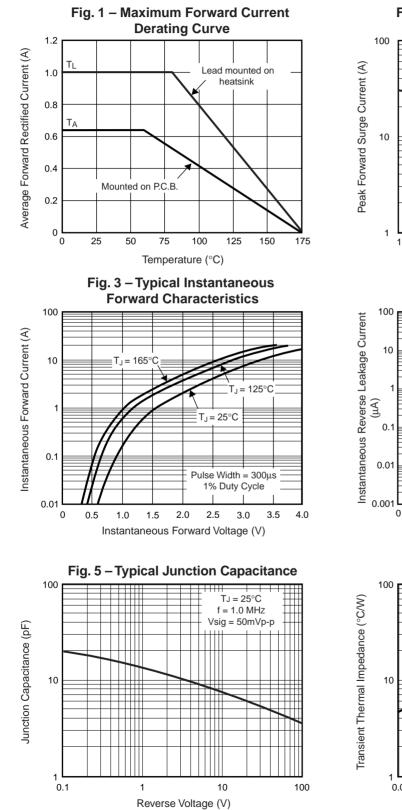


Fig. 2 – Maximum Non-Repetitive Peak forward Surge Current

Fig. 6 – Typical Transient Thermal Impedance

Percent of Rated Peak Reverse Voltage (%)

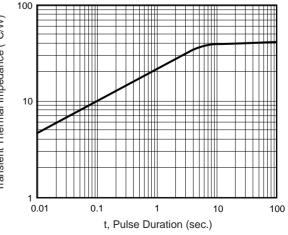
60

80

100

40

20



Document Number 88735 11-Feb-02

Download from www.ICminer.com Electronic-Library Service

